





YJL3400C

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_{D(M)} \in CE$	30	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V,$				



Typical Electrical and Thermal Characteristics Diagrams

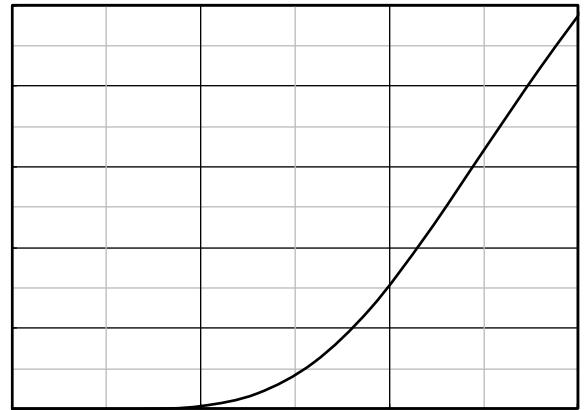


Figure 1.

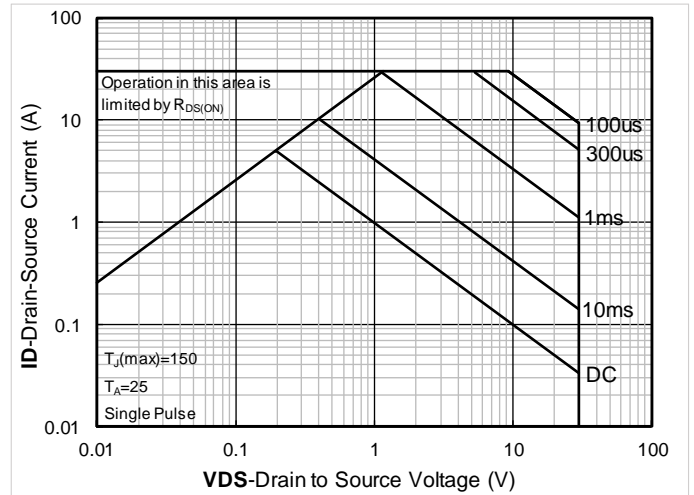


Figure 13. Maximum Transient Thermal Impedance

Figure 14. Safe Operation Area

Test Circuits & Waveforms

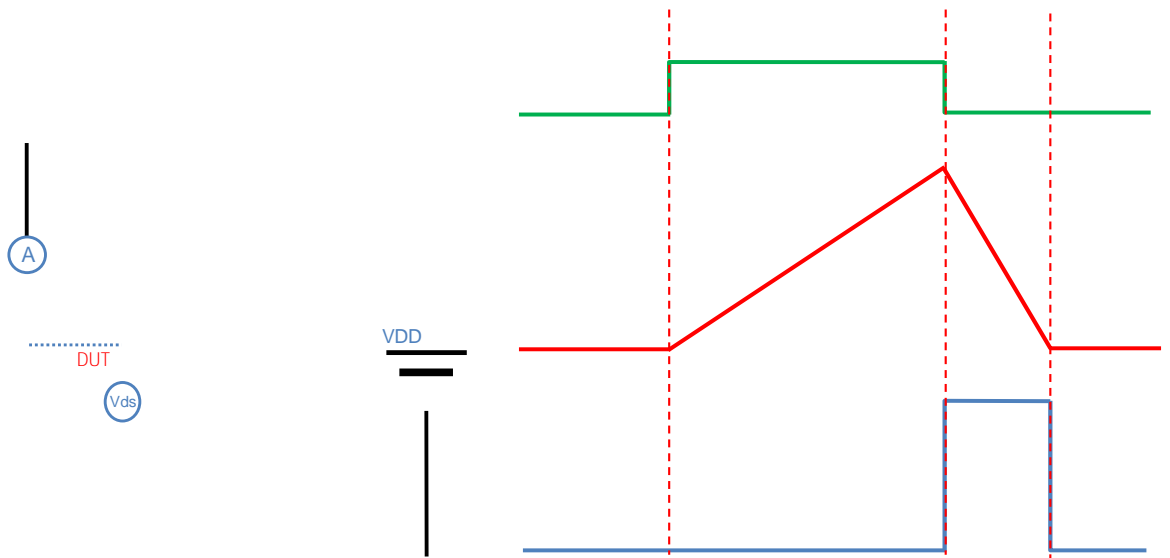


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



Figure B. Gate Charge Test Circuit & Waveform



Figure C. Resistive Switching Test Circuit & Waveform

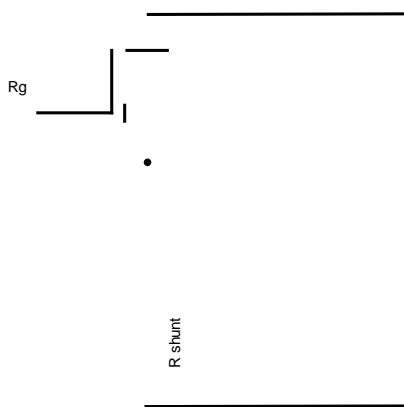
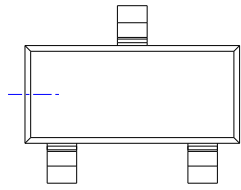


Figure D. Diode Recovery Test Circuit & Waveform



SOT-23 Package information



UNIT mm



YJL3400C

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